

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:	)	
	)	Examiner:
Kazutoshi Kojima et al.	)	
	)	Group Art Unit:
Application No.:	)	
	)	
Corresponding International Filing No.:	)	
PCT/JP2004/011894	)	
	)	
Filed: Herewith	)	
	)	
For: SILICON CARBIDE EPITAXIAL	)	
WAFER, METHOD FOR	)	
PRODUCING SUCH WAFER,	)	
AND SEMICONDUCTOR	)	
DEVICE FORMED ON SUCH	)	
WAFER	)	

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SECOND PRELIMINARY AMENDMENT**

Sir:

Please amend the above-identified patent application as follows.

**Amendments to the Specification** begin on page two of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page four of this paper.

**Remarks** begin on page six of this paper.